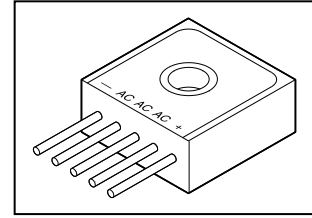


TECHNICAL DATA  
DATA SHEET 1135, REV. B

**THREE PHASE FULL WAVE  
BRIDGE RECTIFIER ASSEMBLY**



DESCRIPTION: A 600 VOLT, 30 AMP, 5000 NANOSECOND THREE PHASE BRIDGE RECTIFIER ASSEMBLY.

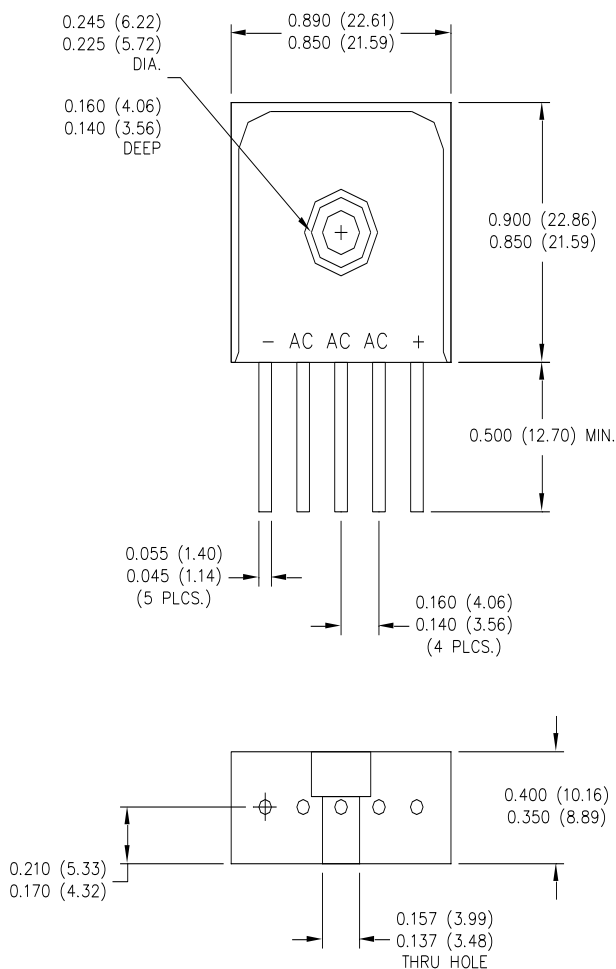
MAX. RATINGS / ELECTRICAL CHARACTERISTICS All ratings are at  $T_A = 25^\circ\text{C}$  unless otherwise specified.

RATING	CONDITIONS	MIN	TYP	MAX	UNIT
Peak Inverse Voltage (PIV)	-	-	-	600	Vdc
Average DC Output Current ( $T_C = \text{Case Temp}$ ) ( $I_o$ )	$T_C = 55^\circ\text{C}$ $T_C = 100^\circ\text{C}$	-	-	30 20	Amps
Peak Single Cycle Surge Current ( $I_{FSM}$ )	$t_p = 8.3 \text{ ms}$ Single Half Cycle Sine Wave, Superimposed On Rated Load	-	-	100	Amps(pk)
Peak Recurring Surge Current ( $I_{FRM}$ )	$T_A = 25^\circ\text{C}$	-	-	75	Amps
Operating and Storage Temp. ( $T_{op}$ & $T_{std}$ )	-	-55	-	+150	$^\circ\text{C}$
Maximum Forward Voltage Per Leg ( $V_f$ )	$I_f = 9.0\text{A}$ dc (300 $\mu\text{sec}$ pulse, duty cycle < 2%)	-	-	1.4	Volts
Maximum Instantaneous Reverse Current At Rated (PIV)	$T_A = 25^\circ\text{C}$ $T_A = 100^\circ\text{C}$	-	-	5.0 100	$\mu\text{Amps}$
Reverse Recovery Time ( $t_{rr}$ )	$I_f = 0.5\text{A}, I_r = 1.0\text{A};$ $I_{rr} = 0.25\text{A}$  Measured on discrete rectifiers prior to assembly.	-	-	5000	nsec
Max. Thermal Resistance ( $R_{\theta JC}$ )	-	-	-	1.50	$^\circ\text{C/W}$

**MECHANICAL DIMENSIONS: In Inches / mm**

**Note:** Case finish - Black Anodized

**Fig. 455**



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